

MR3029-11
Appl. No. 10/057,906
Response to Notice of Non-Compliant Amendment

II. Please amend the original ABSTRACT, page 25, with the following amended ABSTRACT:

ABSTRACT OF THE INVENTION

~~A clean equipment for removing polymer residues on sidewalls of metal lines and method thereof are provided. The present clean equipment comprises a stripping solution bath, at least an organic solvent bath, an overflow bath and a dryer. A gas bubbler and a lattice-like cassette stage are positioned within the organic solvent bath. The gas bubbler provides gas flow in the organic solvent bath to increase the convection of the organic solvent. The lattice-like cassette stage is used for supporting cassettes for carrying wafers. By way of increasing the number of bubbling apertures of the gas bubbler and designing the gas bubbler structure in a way that preventing the bubbling apertures from being blocked by the lattice-like cassette stage, the convection effectiveness of the organic solvent is increased. Thereby, the stripping solution can be effectively removed with the organic solvent. Besides, lengthening the drip dry time of the wafer over each bath so as to eliminate the quantity of the stripping solution left on the wafer drawn in the overflow bath. By the above measures, metal corrosion occurred on the sidewalls of the metal lines formed on the wafer is significantly reduced.~~

A method for removing polymer residues on sidewalls of metal lines is

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provided where a wafer is immersed in a stripping solution for a first immersion time. Next, the wafer is removed from the stripping solution and allowed to drip. Then the wafer is immersed in a first organic solvent for removing the stripping solution left on the wafer. The wafer is then removed from the first organic solvent and allowed to drip. Next, the wafer is immersed in a water flow for removing the stripping solution and the first organic solvent left on the wafer. Finally, water left on the wafer is removed.